

	Hits	Search Text	DBs
31	66	(mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) same (angle or tilt\$4 or rotat\$4 or spin\$4 or slop\$4) same (vary4 or different or adjust or chang\$4 or var\$4 or rang\$4 or oblique)) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and (shadow\$5 or undercut\$4 or overhang) and (((sidewall or side) near22 profile) or hyperbol\$5)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
32	0	360/324.ccls. and (mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
35	1	430/320.ccls. and (mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module)))) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
36	1	(mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) same (angle or tilt\$4 or rotat\$4 or spin\$4 or slop\$4) same (vary4 or different or adjust or chang\$4 or var\$4 or rang\$4 or oblique)) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB

	Hits	Search Text	DBs
37	1	(mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) same (angle or tilt\$4 or rotat\$4 or spin\$4 or slop\$4) same (vary4 or different or adjust or chang\$4 or var\$4 or rang\$4 or oblique)) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and (shadow\$5 or undercut\$4 or overhang) and ((pedestal or pattern or mask) same (first or second or different) same width) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
38	1	(mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) same (angle or tilt\$4 or rotat\$4 or spin\$4 or slop\$4) same (vary4 or different or adjust or chang\$4 or var\$4 or rang\$4 or oblique)) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and (shadow\$5 or undercut\$4 or overhang) and (((sidewall or side) near22 profile) or hyperbol\$5) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
39	0	216/22.ccls. and (mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
40	0	204/192.34.ccls. and (mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module)))) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
33	115	(mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) same (angle or tilt\$4 or rotat\$4 or spin\$4 or slop\$4) same (vary4 or different or adjust or chang\$4 or var\$4 or rang\$4 or oblique)) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and (shadow\$5 or undercut\$4 or overhang) and ((pedestal or pattern or mask) same (first or second or different) same width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
34	1	430/313.ccls. and (mask or pattern or photolithograph\$4 or ((resist or photoresist) near12 (mask or structure or pattern or pedestal))) and (((ion near9 mill\$4) or (ion near9 beam) or IBE or (ion near6 beam near9 source) or (ion near9 source) or (ion near9 (gun or module))) and ((rotat\$4 or mov\$3 or tilt\$4 or spin\$4) same (substrate or wafer)) and ((substrate or wafer or sheet) same (CPP or head or GMR or pedestal)) and (first near12 (GMR or CPP or (read near4 head) or pedestal) near6 width) and (second near5 (pedestal or (GMR near5 stack) or (CPP near9 stack)) near12 width)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB